

Abstract Of The Disclosure

A plasma etching equipment is proposed for especially anisotropic etching a substrate by the action of a plasma. For this purpose, a first, especially inductively coupled plasma-generating device is provided, which has a first means for generating a first high-frequency electromagnetic alternating field, an etching chamber for generating a first plasma from reactive particles by the action of the first high-frequency electromagnetic alternating field upon a first reactive gas with the substrate to be etched, and a first gas supply. A second plasma-generating device is preconnected to this first plasma-generating device, and it has a second means, especially a microwave generator, for generating a second high-frequency electromagnetic alternating field, a plasma-generating region for generating a second plasma from reactive particles by the action of the second high-frequency electromagnetic alternating field upon a second reactive gas, and a second gas supply. In this connection, the generated second plasma of the first plasma-generating device can be supplied at least partially as first reactive gas via the first gas supply.